

SUBSTITUTE FORM PTO-1449
(MODIFIED)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
07043/060002SERIAL NO.
09/342,348INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(Use several sheets if necessary)

AUG 27 1999

APPLICANT:
Brosnahan et al.FILING DATE
6/29/1999GROUP
2812

2814

(37 CFR 1.98(b))

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER							ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.M	AA	3	7	2	5	6	7	1	4/1973	Keister et al.	307	202	
	AB	3	9	3	6	3	2	9	2/1976	Kendall et al.	148	187	
	AC	3	9	6	2	0	5	2	6/1976	Abbas et al.	204	129.3	
	AD	4	0	4	9	9	0	3	9/1977	Kobler	174	68.5	
	AE	4	0	6	3	2	7	1	12/1977	Bean et al.	357	49	
	AF	4	3	0	7	5	0	7	12/1981	Grey et al.	29	380	
	AG	4	3	6	9	5	6	5	1/1983	Muramatsu	29	580	
	AH	4	6	9	8	9	0	0	10/1987	Esquivel	437	52	
	AI	4	7	6	4	6	4	4	8/1988	Reisman et al.	174	68.5	
	AJ	4	8	7	4	4	8	4	10/1989	Foell et al.	204	129.3	
	AK	5	1	2	6	8	1	0	6/1992	Gotou	357	23.6	
	AL	5	1	3	1	9	7	8	7/1992	O'Neill	156	653	
	AM	5	2	6	2	0	2	1	11/1993	Lehmann et al.	204	629.55	
	AN	5	2	7	1	8	0	1	12/1993	Valette	156	653	
	AO	5	7	4	7	3	5	3	5/5/1998	Bashir et al.	437	21	
	AP	5	8	0	7	7	8	3	9/15/1998	Gaul et al.	438	406	

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
A.M	AQ	1-138110	5/1989	Japan				

OTHER DOCUMENTS (including Author, Title, Date, Place of Publication)

A.M	AR	W. Lang et al., "Application of porous silicon as a sacrificial layer," 7th International Conference on Solid - State Sensors and Actuators Digest of Tech. Papers. pp.202-205, Jun 7-10 1993.										
	AS	Gianchandani et al., "MICRON-SIZED, HIGH ASPECT RATIO BULK SILICON MICROMECHANICAL DEVICES," <i>Micro Electro Mechanical Systems</i> '92, 3 pgs., February 4-7, 1992.										

EXAMINER ANH D. MAI DATE CONSIDERED 5/22/01

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. PATENT DOCUMENTS

[illegible]

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							YES	NO

OTHER DOCUMENTS (including Author, Title, Date, Place of Publication)

A.M	BA	C.H. Hsu et al., "MICROMACHINED STRUCTURES FABRICATED USING A WAFER-BONDED SEALED CAVITY PROCESS," Solid-State Sensor and Actuator Workshop Hilton Head, S.Caroline, June 13-16, 1994, 151-155.
	BB	J. Mohan et al., "AN INTEGRATED ACCELEROMETER AS A DEMONSTRATION OF A NEW TECHNOLOGY USING SILICON FUSION BONDING AND DEEP REACTIVE ION ETCHING," Stanford University, Center for Integrated Systems, 21-22.
	BC	L. Parameswaran et al., "Sealed-Cavity Microstructure using Wafer Bonding Technology," The 7th International Conference on Solid-State Sensors and Actuators, 274-277.
	BD	L. Parameswaran et al., "A Merged MEMS-CMOS Process using Silicon Wafer Bonding," IEEE 1995, 4 pgs.
	BE	K.A. Shaw et al., "INTEGRATING SCREAM MICROMACHINED DEVICES WITH INTEGRATED CIRCUITS," IEEE 1996, 44-49.
	BF	K.A. Shaw et al., "SCREAM I: a single mask, single-crystal silicon, reactive ion etching process for microelectromechanical structures", School of Electrical Engineering and National Nanofabrication Facility, Cornell University, Ithaca, NY 14853 (USA)

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